

UTC UNISONIC TECHNOLOGIES CO., LTD

UK4145 Preliminary Power MOSFET

SWITCHING N-CHANNEL POWER MOSFET

DESCRIPTION

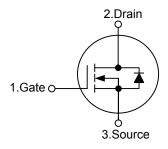
The UTC UK4145 is N-channel power MOSFET, suitable for high current switching applications.

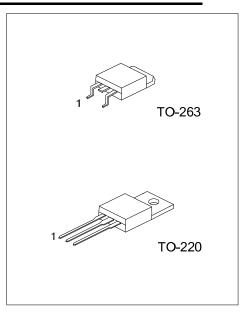
FEATURES

* Low on-state resistance: $R_{DS(ON)} = 10 m\Omega$ (Max.) @ $V_{GS} = 10 V$, $I_{D} = 42 A$

* Low input capacitance: $C_{ISS} = 5300pF (Typ.)$

SYMBOL

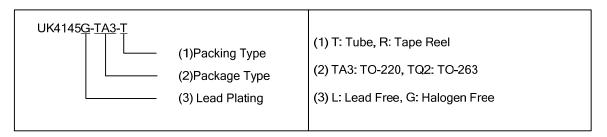




1 of 4

ORDERING INFORMATION

Ordering Number		Daakaga	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UK4145L-TA3-T	UK4145G-TA3-T	TO-220	G	D	S	Tube	
UK4145L-TQ2-T	UK4145G-TQ2-T	TO-263	G	D	S	Tube	
UK4145L-TQ2-R	UK4145G-TQ2-R	TO-263	G	D	S	Tape Reel	



www.unisonic.com.tw QW-R502-364.b

■ **ABSOLUTE MAXIMUM RATINGS** (T_A =25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage (V _{GS} = 0 V)		V_{DSS}	60	V
Gate-Source Voltage (V _{DS} =0 V)		V_{GSS}	±20	V
Drain Current	DC (T _C =25°C)	I_D	±84	Α
	Pulse (Note 2)	I _{DM}	±215	Α
Single Avalanche Current (Note 3)		I _{AS}	32	Α
Single Avalanche Energy (Note 3)		E _{AS}	102	mJ
Power Dissipation (T _A =25°C)		P_D	1.5	W
Junction Temperature		TJ	150	°C
Strong Temperature		T _{STG}	-55 ~ +150	°C

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. PW≤10µs, Duty Cycle≤ 1%
- 3. L = 100 μ H, V_{DD} =30V, R_G =25 Ω , V_{GS} =20 \rightarrow 0V, Starting T_J =25°C,

■ THERMAL DATA

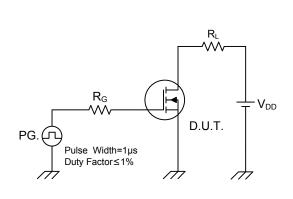
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	83.3	°C/W
Junction to Case	θ_{JC}	1.49	°C/W

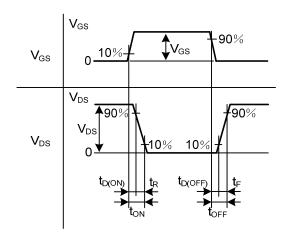
■ **ELECTRICAL CHARACTERISTICS** (T_A =25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	60				
Drain-Source Leakage Current	I_{DSS}	V _{DS} =60V,V _{GS} =0V			10	μΑ	
Gate-Source Leakage Current	I_{GSS}	V_{DS} =0V, V_{GS} =±20V			±100	nA	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(OFF)}$	V_{DS} =10V, I_D =1mA	2.0	3.0	4.0	V	
Drain to Source On-state Resistance (Note)	R _{DS(ON)}	V _{GS} =10 V, I _D =42 A		7	10	mΩ	
DYNAMIC PARAMETERS			_				
Input Capacitance	C _{ISS}			5300		pF	
Output Capacitance	Coss	V _{DS} =10V, V _{GS} =0V, f=1MHz		540		Pf	
Reverse Transfer Capacitance	C _{RSS}			330		pF	
SWITCHING PARAMETERS			_	ā.			
Turn-ON Delay Time	$t_{D(ON)}$			25		ns	
Turn-ON Rise Time	t_R	V_{DD} =30V, V_{GS} =10V		17		ns	
Turn-OFF Delay Time	$t_{D(OFF)}$	I_D =42A, R_G =0 Ω		66		ns	
Turn-OFF Fall-Time	t _F			9		ns	
Total Gate Charge	Q_{G}			90		nC	
Gate Source Charge	Q_GS	V_{DD} =48V, V_{GS} =10V, I_{D} =84A		21		nC	
Gate Drain Charge	Q_GD			30		nC	
SOURCE- DRAIN DIODE RATINGS	AND CHARA	CTERISTICS					
Drain-Source Diode Forward Voltage	\/	V =0V I =94A		1.0	1.5	V	
(Note)	V _{SD}	V _{GS} =0V, I _S =84A		1.0	1.5	V	
Reverse Recovery Time	t_RR	 		43		ns	
Reverse Recovery Charge	Q_{RR}	IS -04A, VGS -0 V, αι/αι - 100A/μS		62		nC	

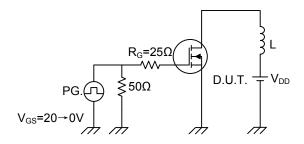
Note: Pulsed

■ TEST CIRCUITS AND WAVEFORMS

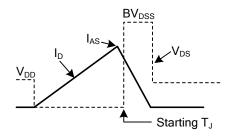




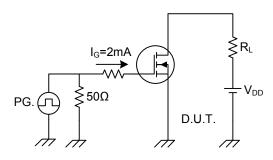
Switching Test Circuit



Switching Waveforms



Unclamped Inductive Switching Test Circuit



Gate Charge Test Circuit

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